

Description:

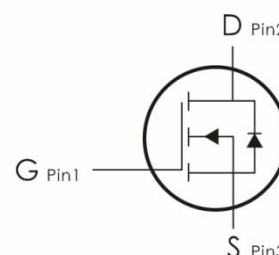
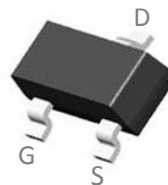
This N-Channel MOSFET uses advanced trench technology and

design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=20V, I_D=8A, R_{DS(ON)} < 14m\Omega @ V_{GS}=4.5V$ (Typ: $11m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DO2320A	2320A	SOT-23-3	3000pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current- $T_A=25^\circ\text{C}$	8	A
	Continuous Drain Current- $T_A=100^\circ\text{C}$	5.6	A
I_{DM}	Pulse Drain Current ^{note1}	32	A
P_D	Power Dissipation- $T_A=25^\circ\text{C}$	1.5	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance-Junction to Case	83.3	$^\circ\text{C/W}$

Electrical Characteristics: ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	20	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =20V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 12V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	0.5	0.75	1.2	V
R _{DS(on)}	Drain-Source on-Resistance	V _{GS} =4.5V, I _D =8A	---	11	14	m Ω
		V _{GS} =2.5V, I _D =5A	---	16	22	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	1200	---	pF
C _{oss}	Output Capacitance		---	175	---	
C _{rss}	Reverse Transfer Capacitance		---	155	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =10V, V _{GS} =4.5V, I _D =4A, R _G =3 Ω	---	9	---	ns
t _r	Rise Time		---	25	---	ns
t _{d(off)}	Turn-Off Delay Time		---	37	---	ns
t _f	Fall Time		---	14	---	ns
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =4A	---	15	---	nC
Q _{gs}	Gate-Source Charge		---	2	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	5.2	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Forward Voltage	V _{GS} =0V , I _S =8A	---	---	1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature2.

2. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

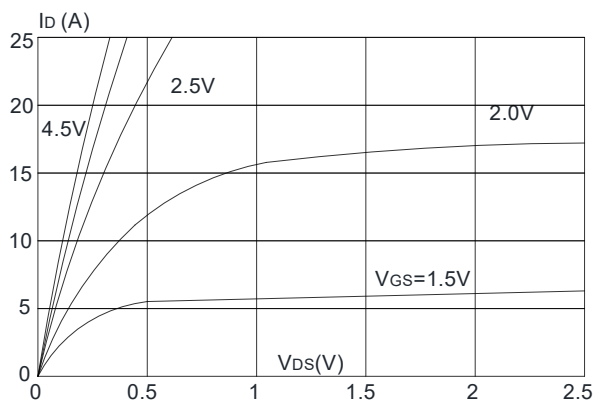


Figure1: Output Characteristics

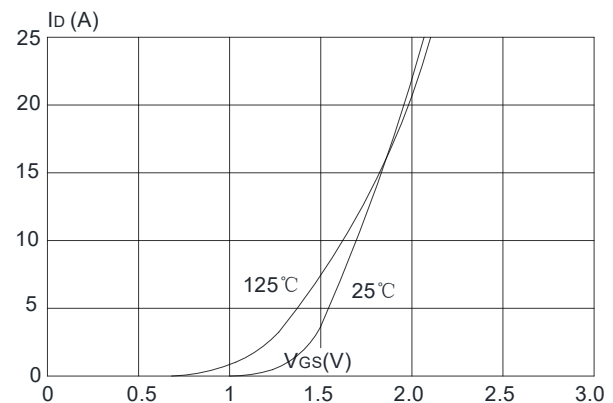


Figure 2: Typical Transfer Characteristics

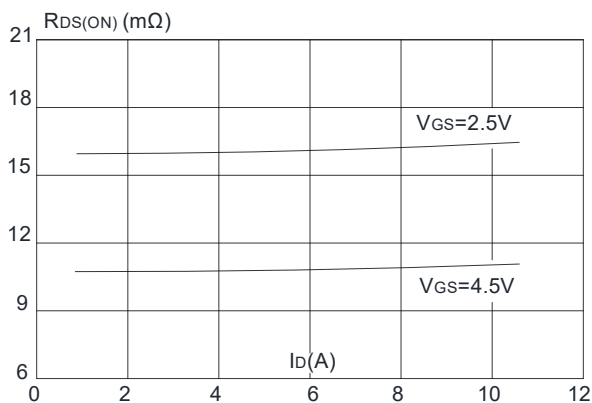


Figure 3: On-resistance vs. Drain Current

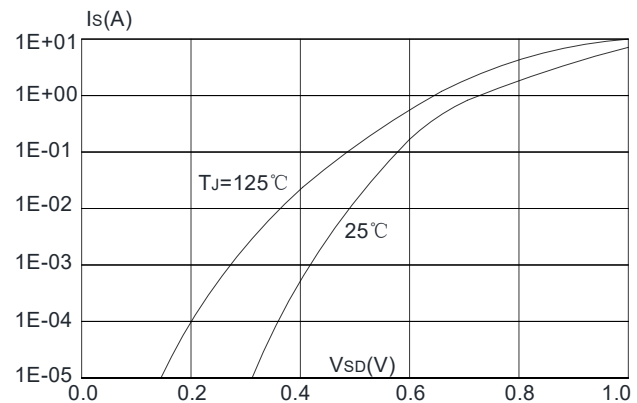


Figure 4: Body Diode Characteristics

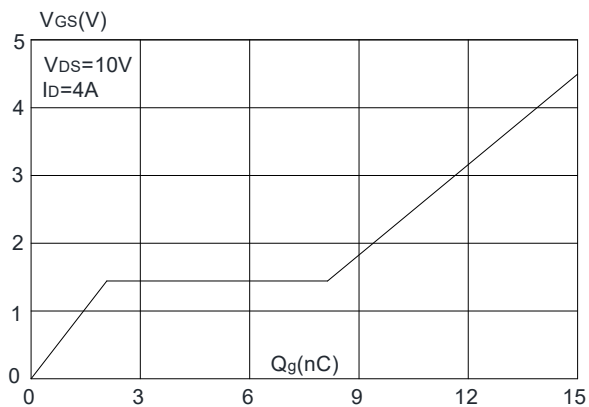


Figure 5: Gate Charge Characteristics

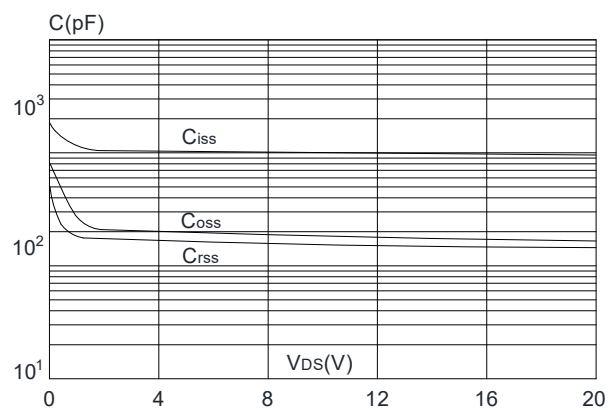


Figure 6: Capacitance Characteristics

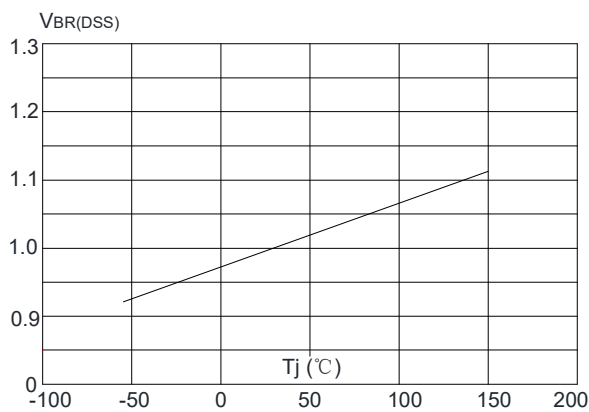


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

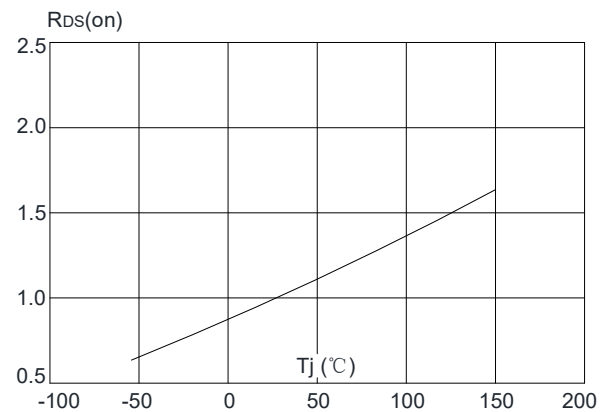


Figure 8: Normalized on Resistance vs. Junction Temperature

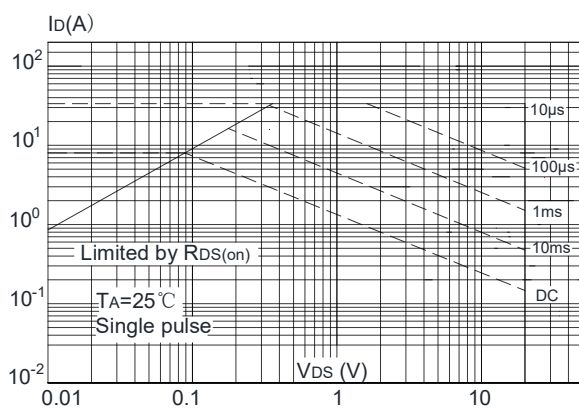


Figure 9: Maximum Safe Operating Area

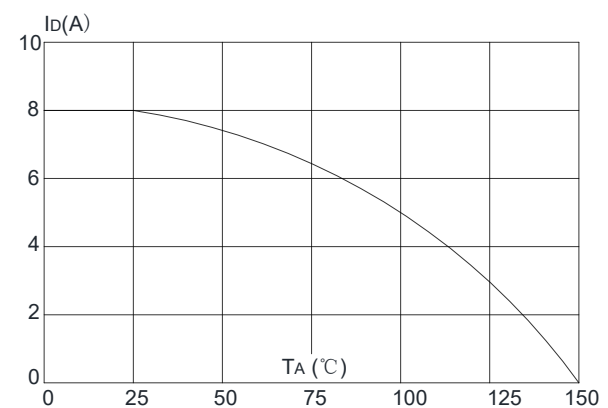


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

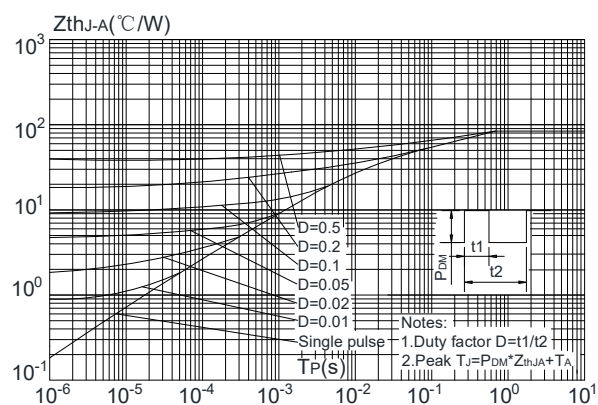
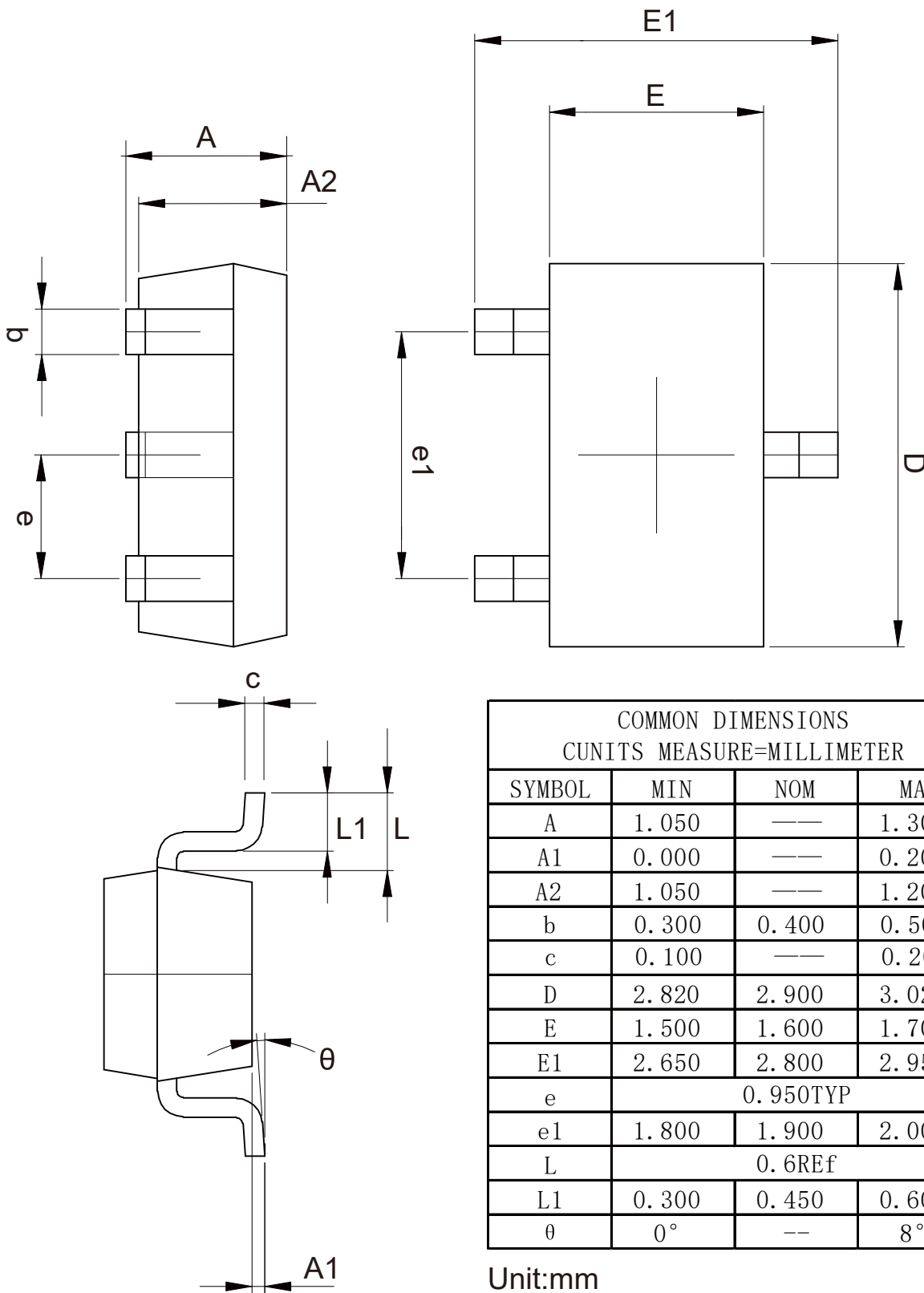
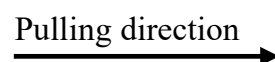
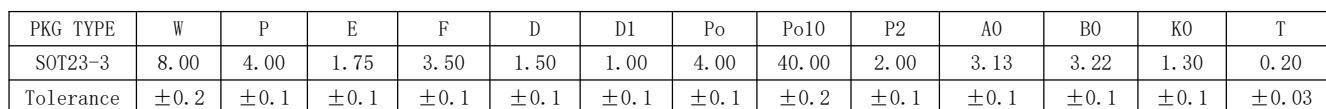


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

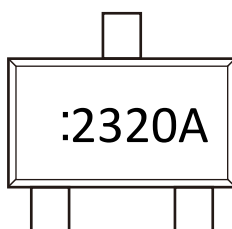
SOT-23-3 Package Outline Data



Dimensions in mm



Marking Information:



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2026-02-06	Release of final version

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